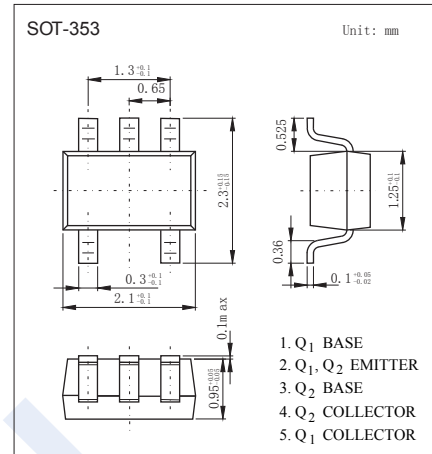
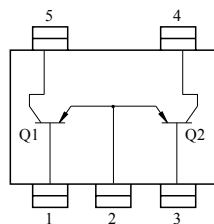


PNP Transistors

KTA501U

■ Features

- Excellent temperature response between these 2 transistor.
- High pairing property in hFE.
- The following characteristics are common for Q1, Q2.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CBO}	-50	V
Collector - Emitter Voltage	V _{CEO}	-50	
Emitter - Base Voltage	V _{EBO}	-5	
Collector Current - Continuous	I _C	-150	mA
Base Current	I _B	-30	
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CBO}	I _C = -100 μA, I _E = 0	-50			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -1 mA, I _B = 0	-50			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 μA, I _C = 0	-5			
Collector-base cut-off current	I _{CBO}	V _{CB} = -50 V, I _E = 0			-0.1	uA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C = 0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -100 mA, I _B = -10mA			-0.3	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C = -100 mA, I _B = -10mA			-1.2	
DC current gain	h _{FE}	V _{CE} = -6V, I _C = -2mA	120		400	
Noise Figure	NF	V _{CE} = -6V, I _C = -0.1mA, f = 1KHz, R _g = 10KΩ			10	dB
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz			7	pF
Transition frequency	f _T	V _{CE} = -10V, I _C = -1mA	80			MHz

■ Classification of hfe

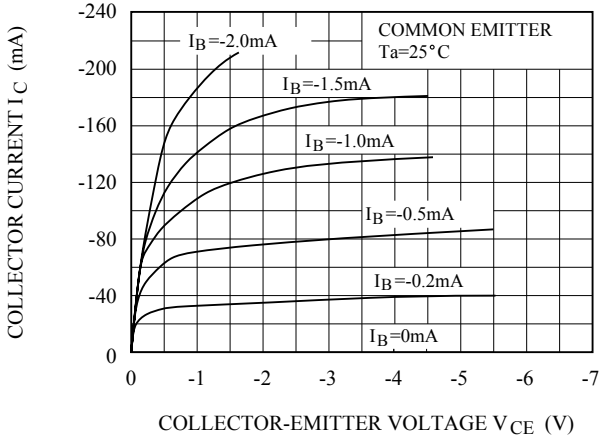
Type	KTA501U-Y	KTA501U-G
Range	120-240	200-400
Marking	SY	SG

PNP Transistors

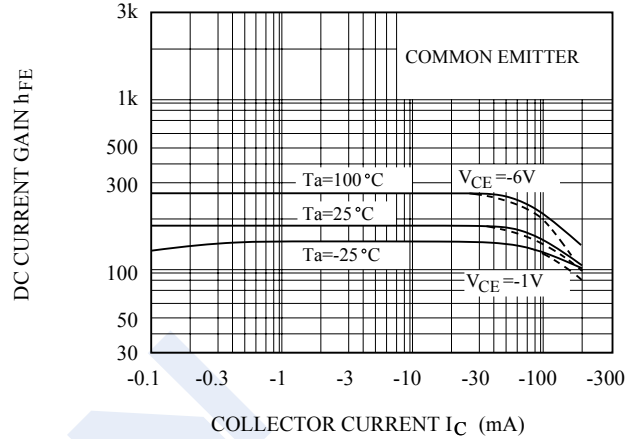
KTA501U

■ Typical Characteristics

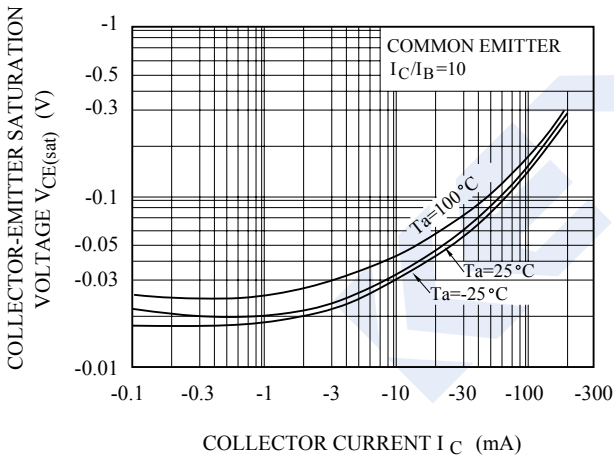
$I_C - V_{CE}$



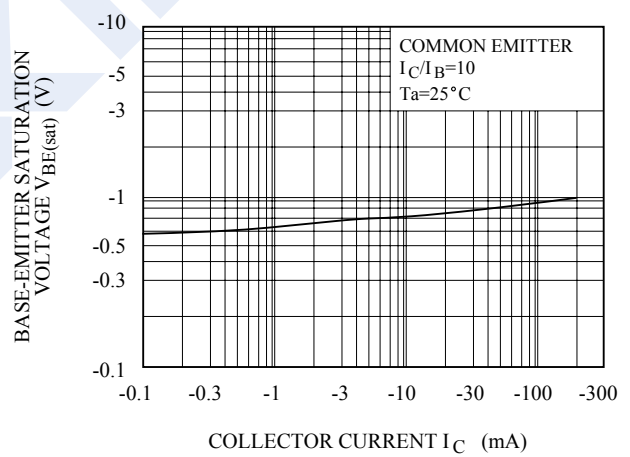
$h_{FE} - I_C$



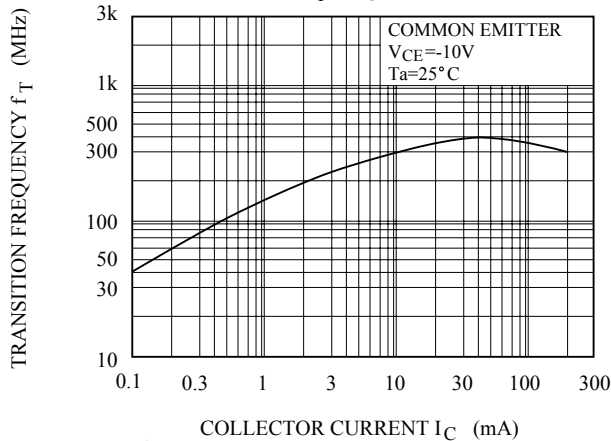
$V_{CE(sat)} - I_C$



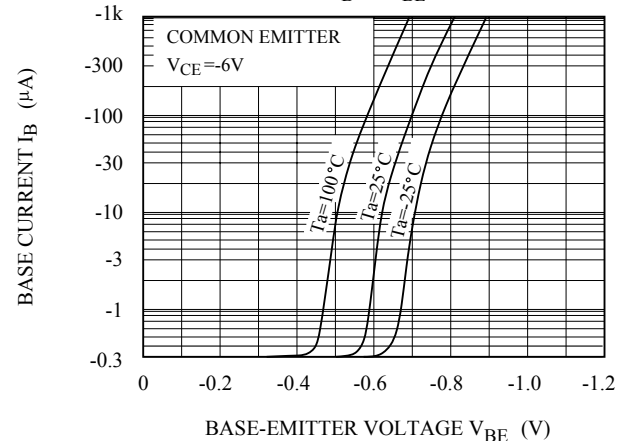
$V_{BE(sat)} - I_C$



$f_T - I_C$



$I_B - V_{BE}$



PNP Transistors

KTA501U

■ Typical Characteristics

